moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam during directing said pulsed laser beam to said glass substrate, thereby irradiating said semiconductor islands with said pulsed laser beam.

2. (Previously Amended) A method according to claim 1 wherein an energy density of said pulsed laser beam is not higher than 300 mJ/cm^2.

3. (Original) A method according to claim 1 wherein an impurity selected from the group consisting of phosphorus and boron is selectively introduced into said plurality of semiconductor islands by said ion doping.

4. (Previously Amended) A method according to claim 1 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed laser beam.

5. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a glass substrate;

crystallizing said semiconductor film;

patterning the crystallized semiconductor film into a plurality of semiconductor islands;

subjecting said semiconductor islands to an ion doping;

directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam during directing said pulsed laser beam to said glass substrate, thereby irradiating said semiconductor islands with said pulsed laser beam.

6. (Previously Amended) A method according to claim 5 wherein an energy density of said pulsed laser beam is not higher than 300 mJ/cm^2.

7. (Original) A method according to claim 5 wherein an impurity selected from the group consisting of phosphorus and boron is selectively introduced into said plurality of semiconductor islands by said ion doping.

8. (Previously Amended) A method according to claim 5 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed laser beam.

9. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of first semiconductor islands and a plurality of second semiconductor islands over a glass substrate;

subjecting both of said first and second semiconductor islands to a first ion doping for introducing a first impurity;

subjecting only said first semiconductor islands to a second ion doping for introducing a second impurity wherein said second impurity has an opposite conductivity type to said first impurity;

directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam during directing said pulsed laser beam to said glass substrate, thereby irradiating both of said first and second semiconductor islands with said pulsed laser beam.

10. (Previously Amended) A method according to claim 9 wherein an energy density of said pulsed laser beam is not higher than 300 mJ/cm^2.

11. (Original) A method according to claim 9 wherein said first impurity is phosphorus while said second impurity is boron.

12. (Previously Amended) A method according to claim 9 wherein each of said first and second semiconductor islands is irradiated with plural pulses of said pulsed laser beam.

13. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands over a glass substrate;

forming a film comprising silicon oxide over said glass substrate wherein said semiconductor islands are covered by said film;

subjecting said semiconductor islands to an ion doping through said film;

directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam during directing said pulsed laser beam to said glass substrate, thereby irradiating said semiconductor islands with said pulsed laser beam through said film.

14. (Previously Amended) A method according to claim 13 wherein an energy density of said pulsed laser beam is not higher than 300 mJ/cm^2.

15. (Original) A method according to claim 13 wherein an impurity selected from the group consisting of phosphorus and boron is selectively introduced into said plurality of semiconductor islands by said ion doping.

16. (Previously Amended) A method according to claim 13 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed laser beam.

17. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands comprising silicon and germanium over a substrate;

subjecting said semiconductor islands to an ion doping;

directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam during directing said pulsed laser beam to said glass substrate, thereby irradiating said semiconductor islands with said pulsed laser beam.

18. (Original) A method according to claim 17 wherein an impurity selected from the group consisting of phosphorus and boron is selectively introduced into said plurality of semiconductor islands by said ion doping.

19. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands comprising silicon and germanium over a substrate;

forming a film comprising silicon oxide over said glass substrate wherein said semiconductor islands are covered by said film;

subjecting said semiconductor islands to an ion doping through said film;

directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam during directing said pulsed laser beam to said glass substrate, thereby irradiating said semiconductor islands with said pulsed laser beam through said film.

20. (Original) The method of manufacturing a semiconductor device according to claim 19 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed excimer laser beam.

21. (Previously Added) The method of claim 1, wherein said pulsed laser beam is a pulsed excimer laser beam.

22. (Previously Added) The method of claim 5, wherein said pulsed laser beam is a pulsed excimer laser beam.

23. (Previously Added) The method of claim 9, wherein said pulsed laser beam is a pulsed excimer laser beam.

24. (Previously Added) The method of claim 13, wherein said pulsed laser beam is a pulsed excimer laser beam.

25. (Previously Added) The method of claim 17, wherein said pulsed laser beam is a pulsed excimer laser beam.

26. (Previously Added) The method of claim 19, wherein said pulsed laser beam is a pulsed excimer laser beam.